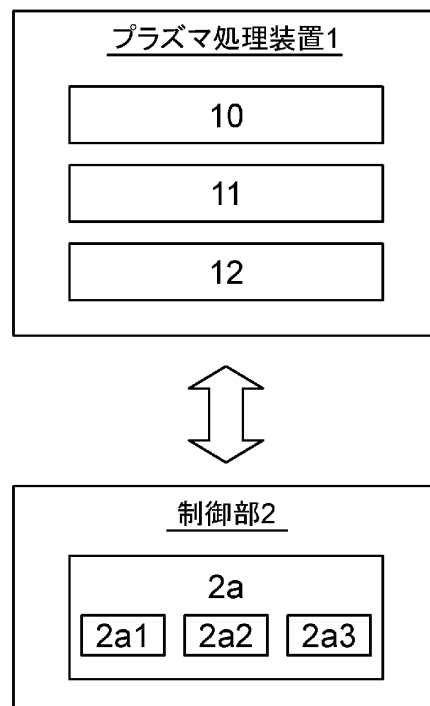
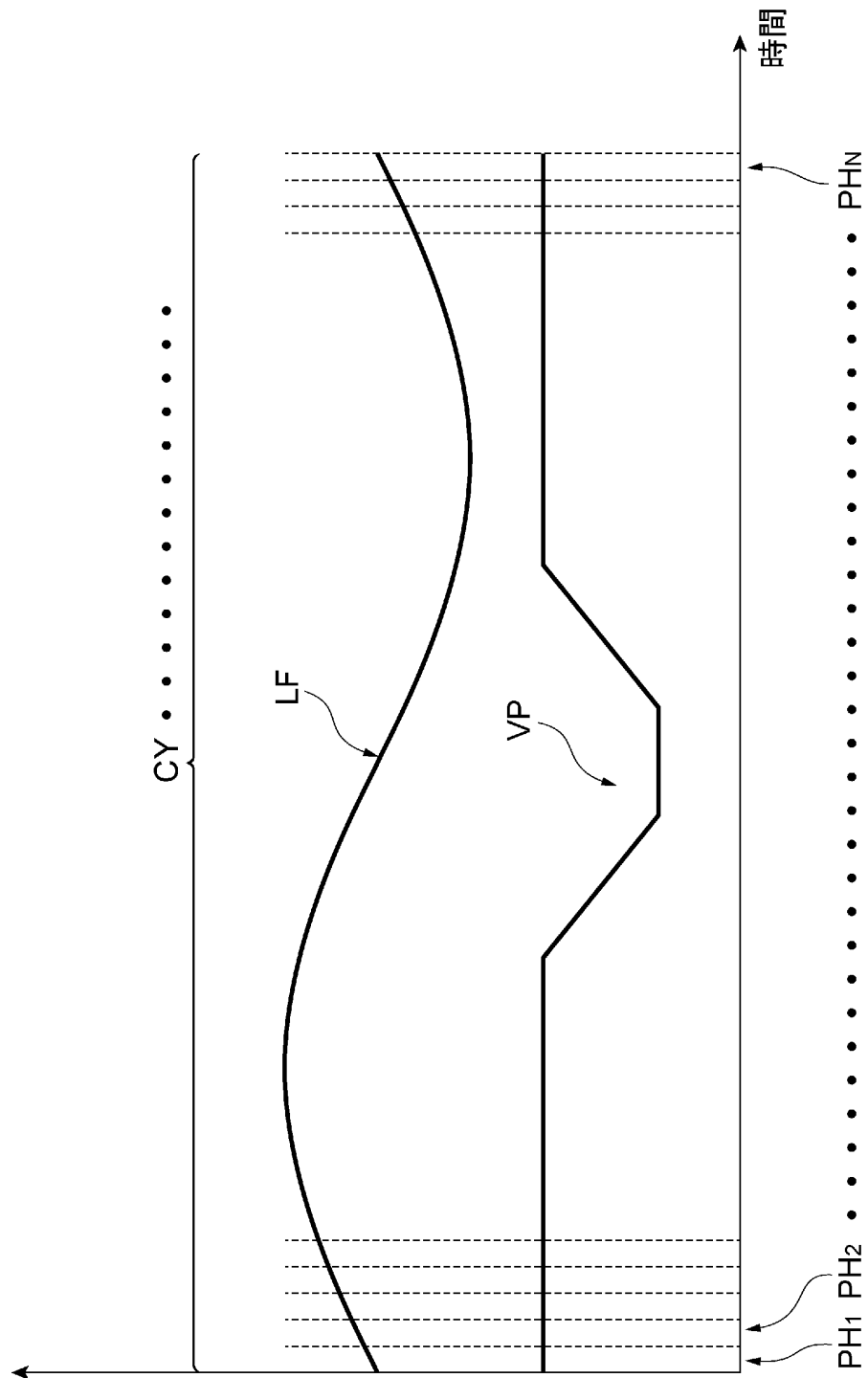


[図1]

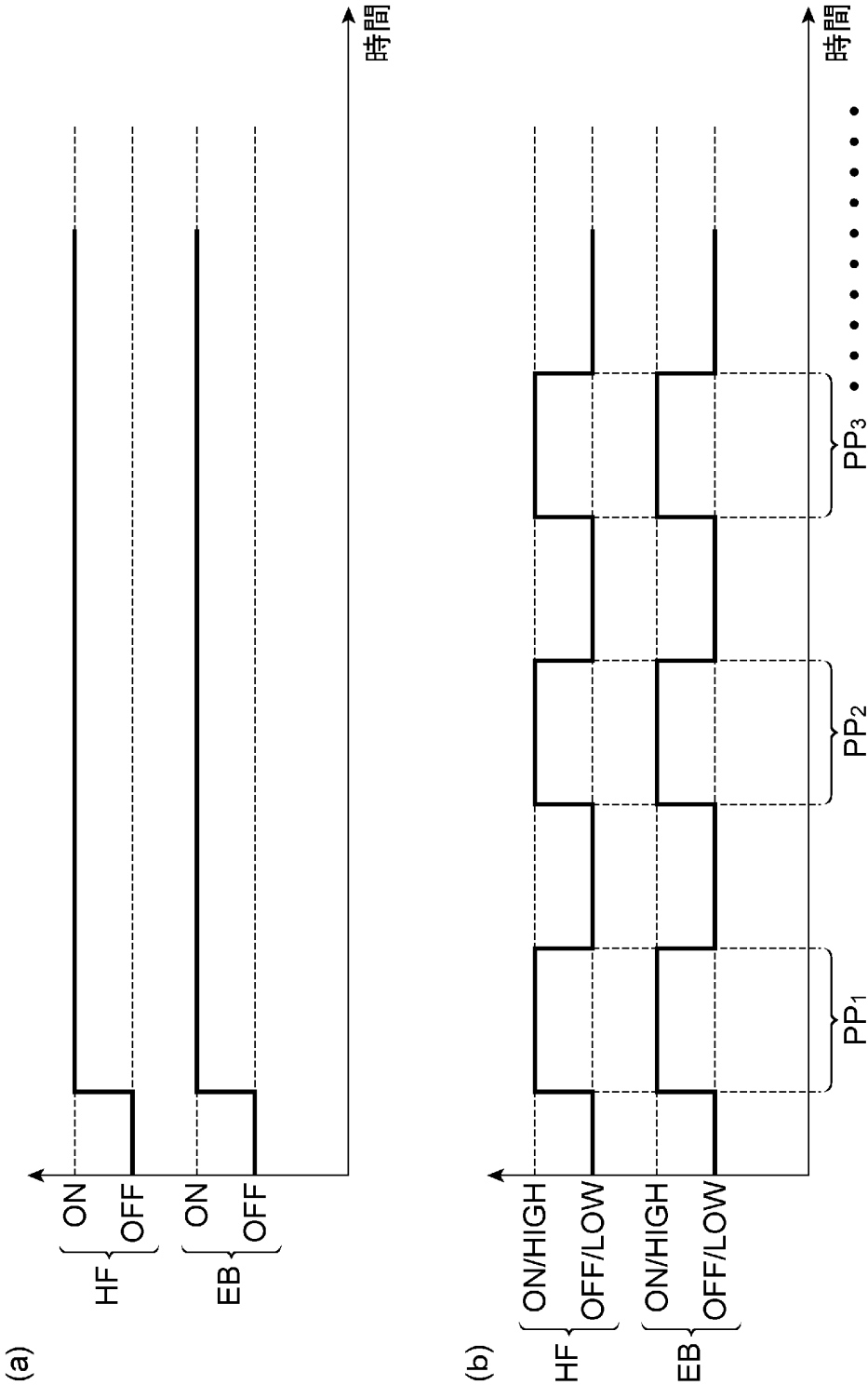


The schematic diagram illustrates a plasma processing apparatus 1. A main chamber 10 contains a substrate 11 supported by a pedestal 110. The pedestal 110 includes a lower electrode 111a and an upper electrode 111b, which are connected to a power supply 30 via a matching network 31. The power supply 30 provides RF power (HF) and electron beam power (EB). The EB is generated by an electron gun assembly 40, which includes a cathode 41, a grid 42, and an anode 43. The electron gun assembly 40 is connected to a power supply 34. The main chamber 10 is surrounded by a cooling jacket 10e, which is connected to a water inlet/outlet 10f. A gas inlet system 20 is also shown, including a gas cylinder 21 and a flow controller 22, which feeds gas into the main chamber 10 through a gas inlet 23. A pressure sensor 24 is located in the main chamber 10. A control unit 38 is connected to various components, including the power supply 30, the electron gun assembly 40, the gas inlet system 20, and the pressure sensor 24.

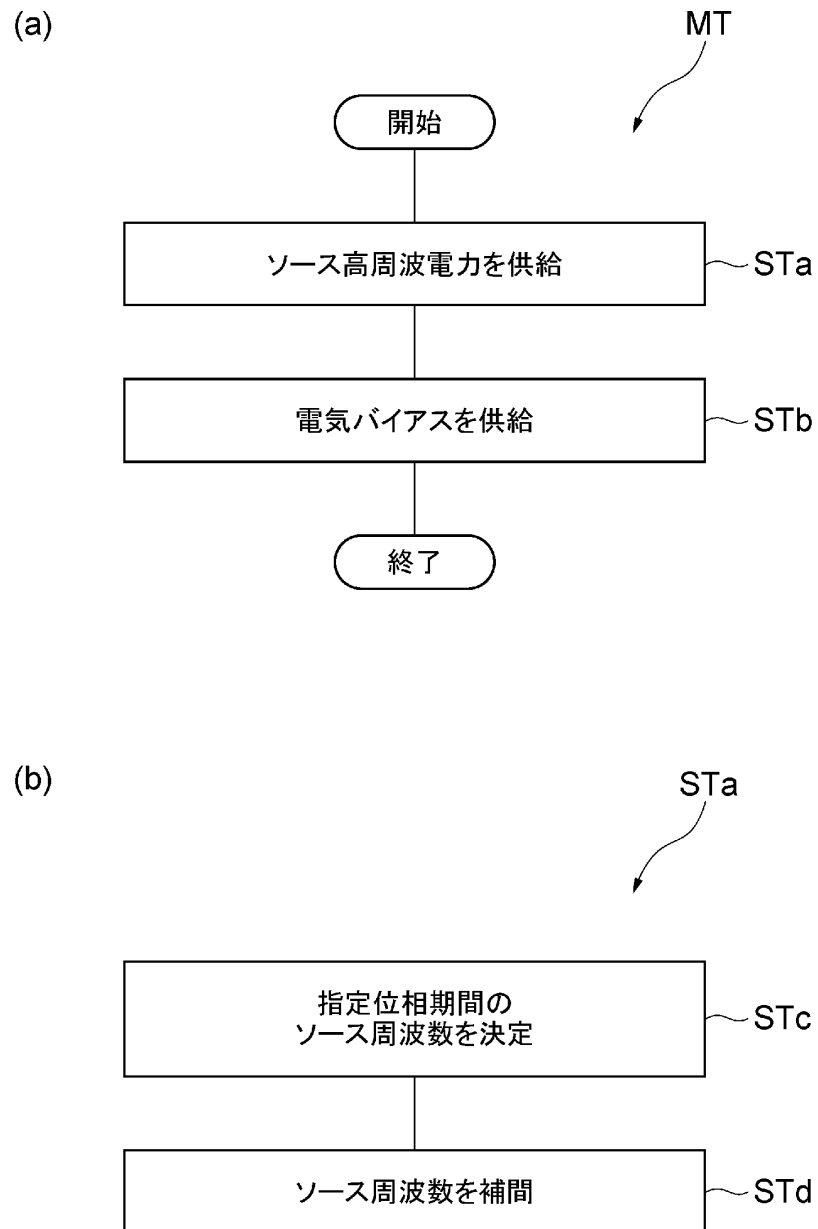
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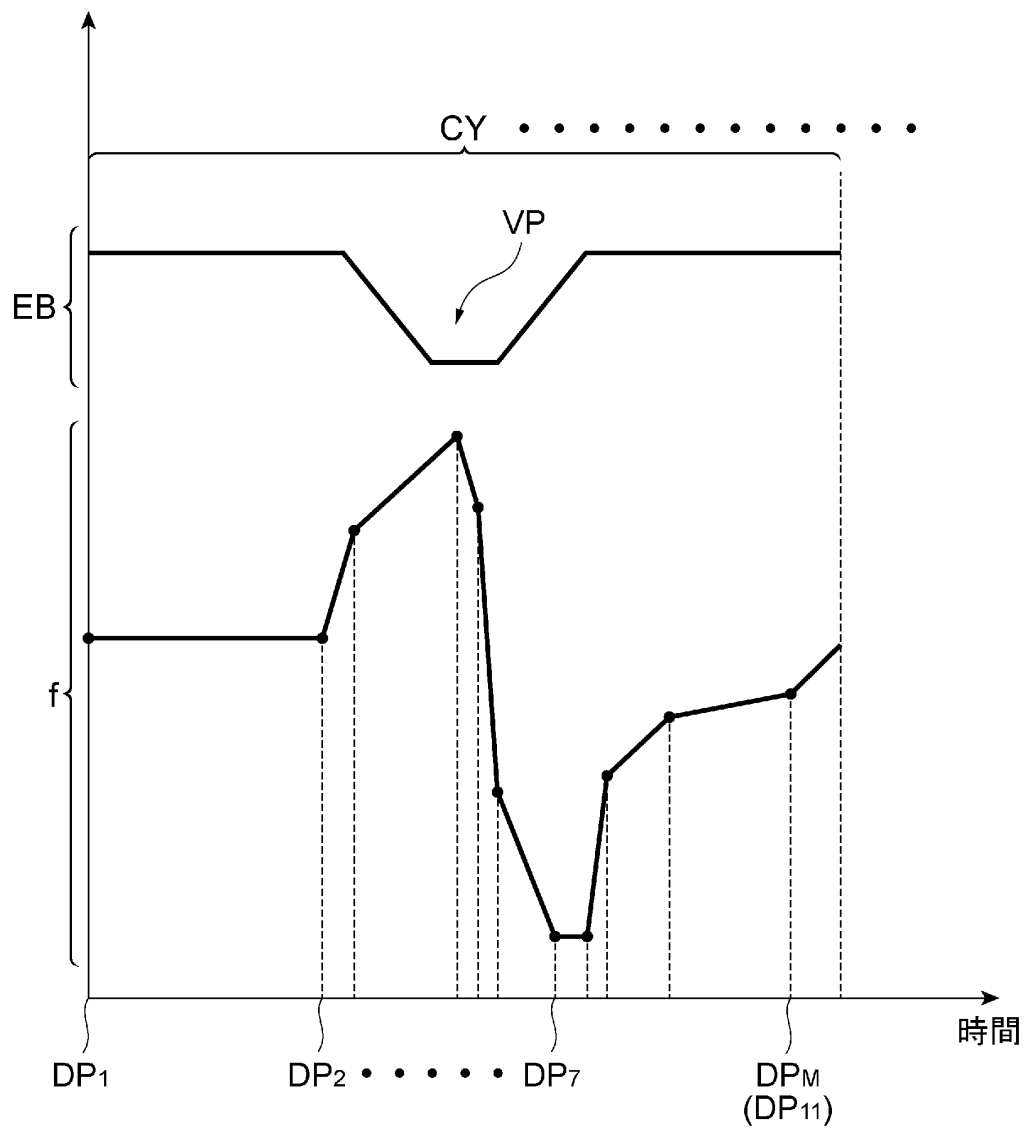
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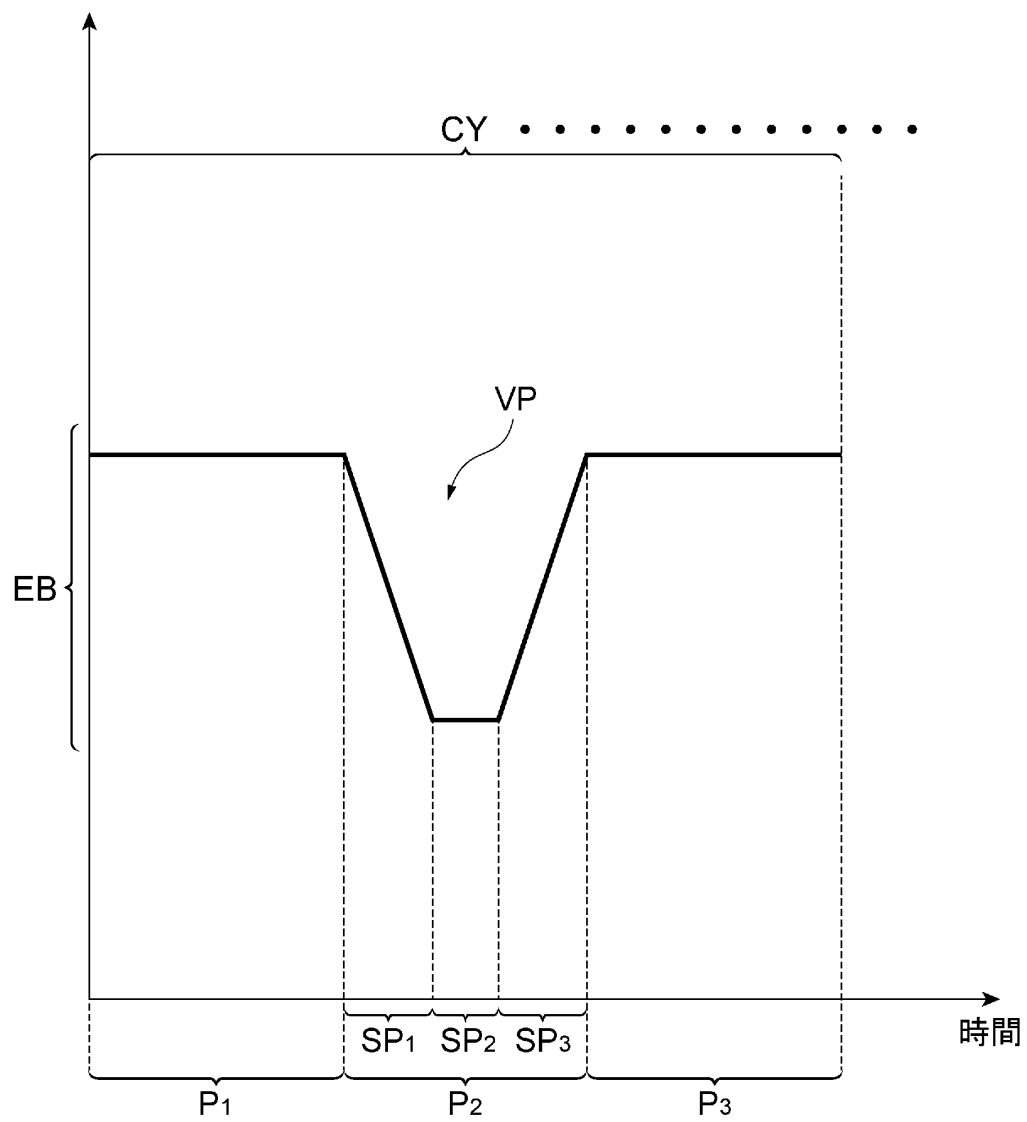
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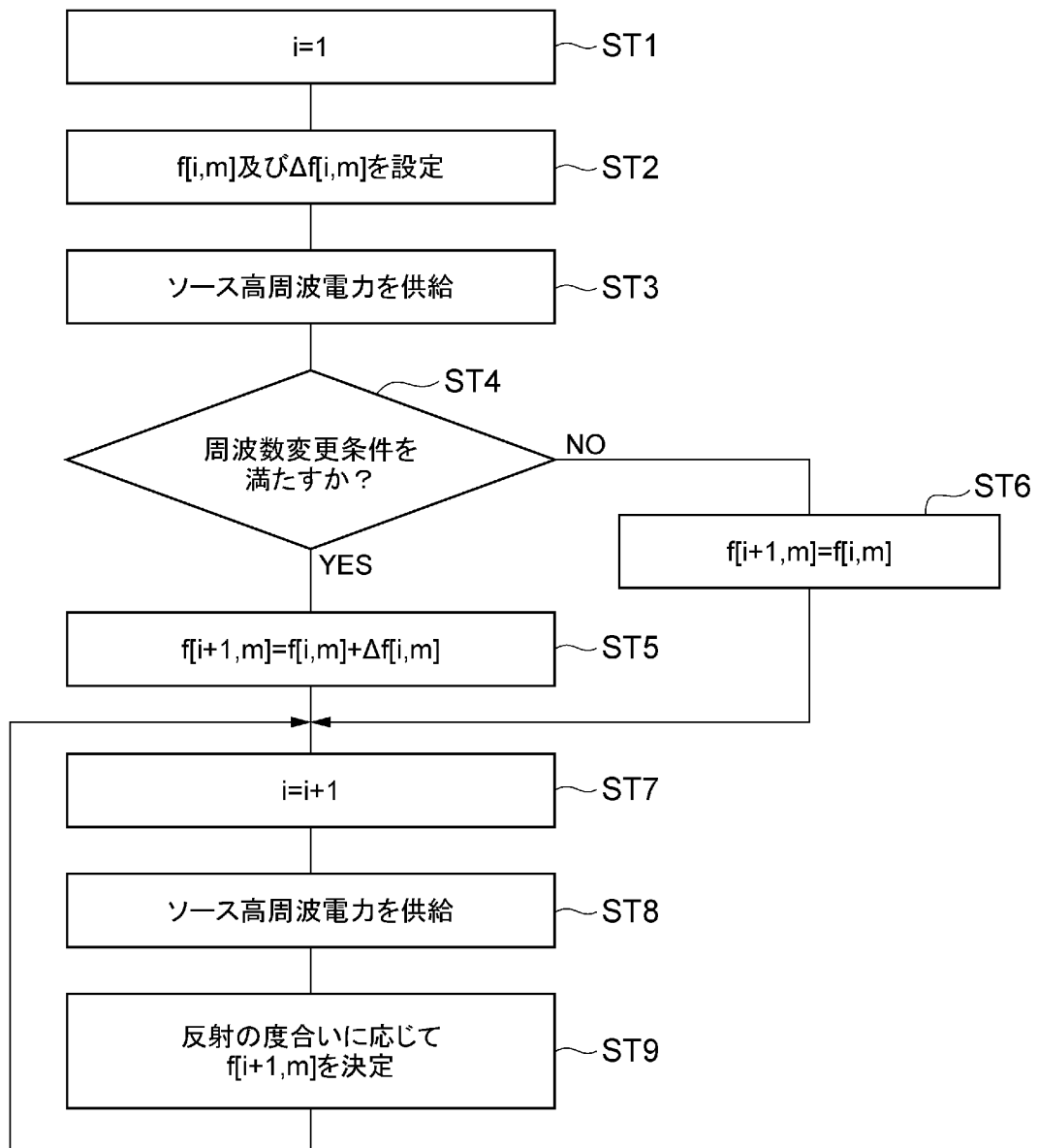
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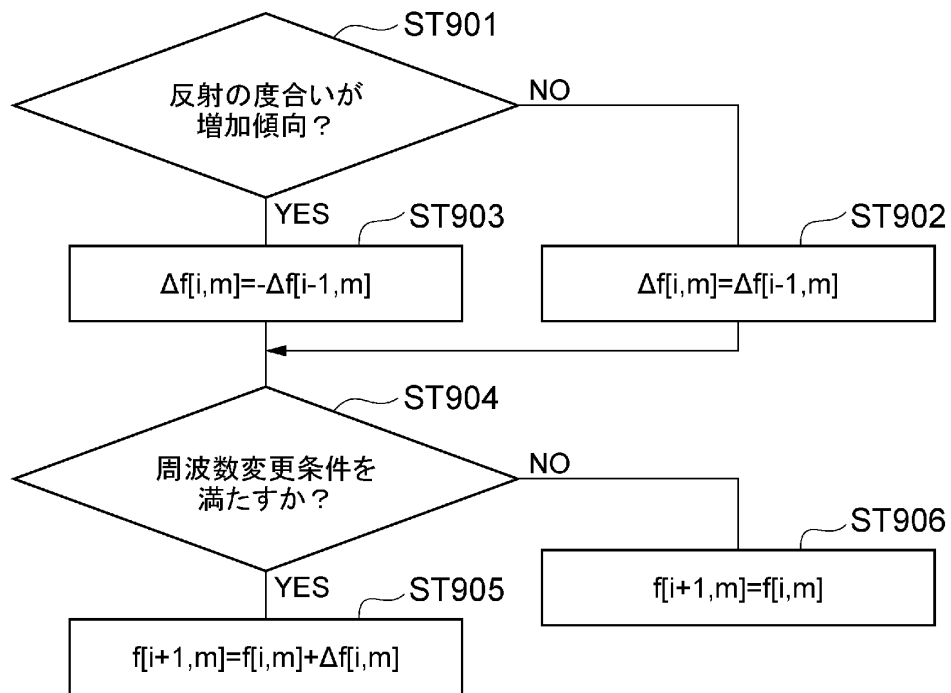
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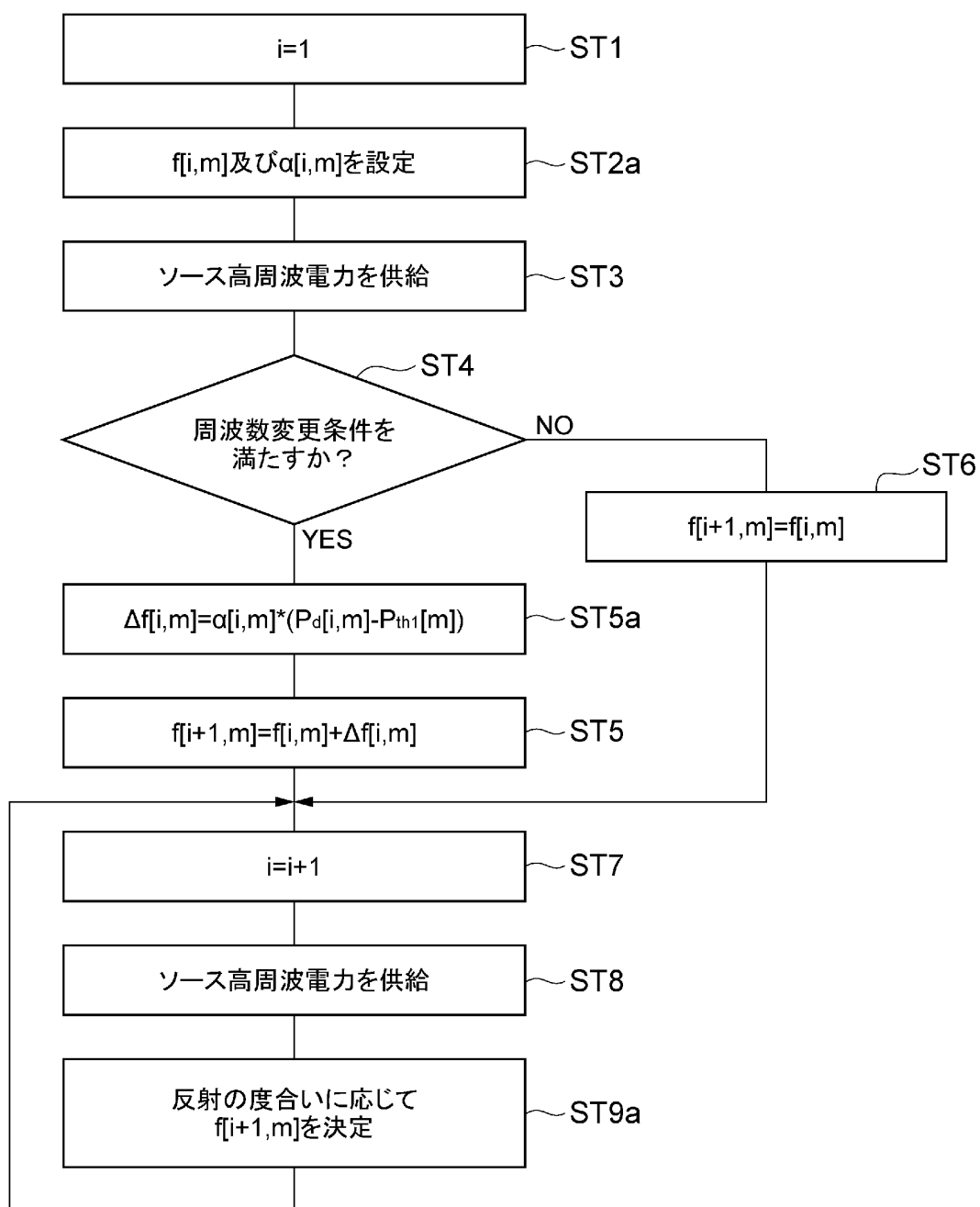
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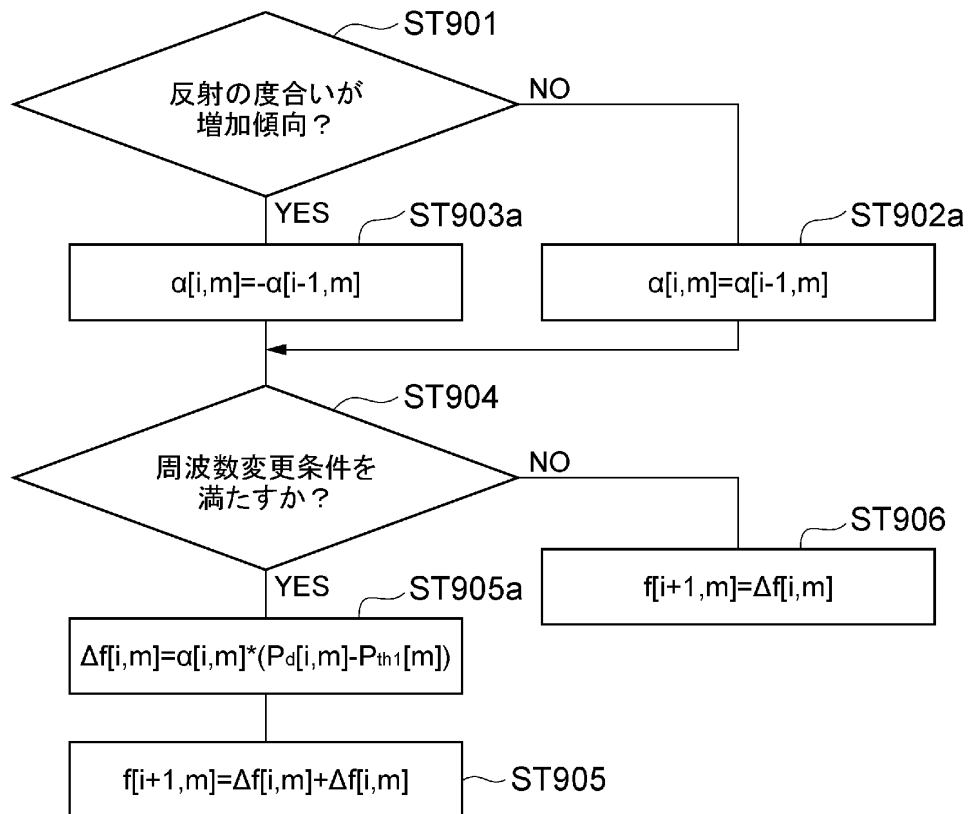
[図9]



[図10]



[図11]



[図12]

